

STRAIN-SENSITIVITY OF STRUCTURES
OF THE Au– Si⟨Ni⟩– Sb TYPE
AT UNIFORM PRESSURE

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S u m m a r y

We research the strain-sensitivity of structures with Shottky barriers made on the basis of Si⟨Ni⟩ with different specific resistance. It is shown that maximal strainsensitivity is observed in structures whose bases have specific resistance equal to $\rho = 10^3$ Ohm·cm. It is shown that the strain-sensitivity depends on the applied voltage and has a maximal value under the voltage $U = 2,5$ V.